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最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 ($T_c=25^\circ\text{C}$)					電 気 的 特 性 ($T_c=25^\circ\text{C}$)										外 形	備 考	
				V_{ce0} (V)	V_{be0} (V)	I_c (mA)	P_c (mW)	T_c ($^\circ\text{C}$)	I_{c0} 最大値 (μA)	直流又はパルス h_{FE}		バイアス		h_{FE}	h_{ie} h_{ie}^* (Ω)	h_{re} h_{re}^* ($\times 10^{-4}$)	h_{oe} h_{oe}^* (μS)	$f_{\alpha b}$ $f_{\alpha b}^*$ (Mc)			C_{ob} (pF)
1	2	3	4	5					6		7		8				9	10		11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE} , I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB} , I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9 $f_{\alpha b}$ OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_T .
- 10 C_{ob} AND $r_{bb'}$ OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN $r_{bb'}$ COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11 OUTLINE
- 12 REMARKS

:とコンプリ: COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電 気 的 特 性 (T _a = 25°C)											外形	備考									
				V _{CEO} (V)	V _{EB0} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CEO} 最大値 (μA)	V _{CEB} (V)	直流又はパルス h _{FE}	バイアス	h _{FE}	h _{ib} *	h _{re}	h _{rb} *	h _{oe} *	f _{αB} f _T * (Mc)	C _{ob} (pF)			τ _{bb} (real)* (Ω)								
2SCI751																														
" 1752	モトローラ	RF	Si. E	300	6	500	625	150	0.1	200	125	10	10	20	-10	モトローラ MP6A42 相当	80 *	1.7	C _o τ _{bb} 300pS	138D										
" 1753	"	"	"	200	6	500	625	150	0.1	160	125	10	10	20	-10	" MPSA43 "	80 *	1.7	C _o τ _{bb} 300pS	138D										
" 1754	"	"	"	40	12	500	625	150	0.05	30	100k	5	10	5	-10	JEDEC 2N6426 "	240 *	5.4	1 M *	138D										
" 1755	三洋	PA	Si.TP	300	7	200	15W (T _c =25°C)	150	0.1	200	40~200	10	10	30	-10		>50 *	<5.3		268										
" 1756	"	"	"	300	7	200	15W (T _c =25°C)	150	0.1	200	40~200	10	10	30	-10		>50 *	<5.3		300										
" 1757	"	"	"	300	7	200	15W (T _c =25°C)	150	0.1	200	40~200	10	10	30	-10		>50 *	<5.3		267										
" 1758	日電	RF	Si. T	300	7	100	10W (T _c =25°C)	150	1	300	120	10	20	20	-10		80 *	<3		104										
" 1759																														
" 1760	ソニー	RF. PA	Si. E	100	6	1 A	950		0.2	25	250	2	100	2	-10		80 *	16	C _o τ _{bb} 300pS	174B										
" 1761	"	"	"	20	6	2 A	950	120	0.1	16	320	2	100	2	-10		80 *	30	C _o τ _{bb} 300pS	174B	2SA861 とコンプリ									
" 1762	"	SW	Si. T	700	12	300	470	150	2	100	50	5	10	5	-10	t _c =350nS t _{trf} =600nS t _r =250nS t _f =250nS	13 *	8.5	C _o τ _{bb} 200pS	181	2SA911 とコンプリ									
" 1763	東芝	PA	Si. EP	65	4	7 A	80W (T _c =25°C)	175	3mA	30	>10	10	5 A	15	-100	P ₀ =45W (PEP) (f=30MHz, V _{CC} =28V, P _i =1W)	>50 *	110		281										
" 1764	"	"	"	65	4	12 A	140W (T _c =25°C)	175	6mA	30	>10	10	10A	15	-200	P ₀ =85W (PEP) (f=30MHz, V _{CC} =28V, P _i =2.84W)	>50 *	220		281										
" 1765	"	"	"	35	3.5	800	7.5W (T _c =25°C)	175	1mA	15	>10	5	500			P ₀ =3.2W (f=470MHz, V _{CE} =12.6V, P _i =0.6W)	<15		97C	エミッタ ベース接続										
" 1766	日立	AF	Si. EPa	30	5	100	310	125	0.5	18	600	12	2	12	-2	NF=4dB (1kHz, 6V, 0.1mA)	230 *	1.8		138D	2SA1033 とコンプリ									
" 1767																														
" 1768	サンケン	PA	Si.TMe	200	6	5 A	50W (T _c =25°C)	150	100	200	1000	4	1 A	12	-100		15 *	50	100 *	102										
" 1769	新日無	RF. LN	Si. EP	30	5	50	200	125	0.05	20	250	6	1	6	-0.1		50 k	5	1b	200 *	2	C _o τ _{bb} 60pS	138D							
" 1770	"	RF. AF	"	30	5	200	300	125	0.1	20	250	6	1	6	-1		5 k	1	20	100 *	5	C _o τ _{bb} 40pS	138D							
" 1771	"	RF	"	60	5	200	300	125	0.1	20	250	6	1	10	-2					100 *	5	C _o τ _{bb} 40pS	138D							
" 1772	"	"	"	95	5	50	300	125	0.1	20	250	6	1	10	-2					40 *	5	C _o τ _{bb} 40pS	138D							
" 1773	"	"	"	30	5	400	500	125	0.5	20	200	1	100	10	-5					100 *	6	C _o τ _{bb} 50pS	138D							
" 1774	"	"	"	60	5	400	500	125	0.5	20	200	1	100	10	-5					100 *	6	C _o τ _{bb} 50pS	138D							
" 1775	日立	"	Si. E	90	5	50	300	125	0.5	75	400~1200	12	2	12	-2					200 *	1.6		138	2SA872 とコンプリ						
" 1776	富士通	"	Si. EP	60	6	200	300	150	0.5	40	150	1	10	10	-10					220 *	3	40 *	275							
* 1777	サンケン	PA	Si. EMe	70	6	6 A	50W (T _c =25°C)	150	1mA	70	60	4	5 A	12	-500					10 *	90	12 *	102							
" 1778	松下	RF. Conv. Osc	Si. P	25	3	15	150	125	100	25	50	10	3	10	-3					650 *	1	30 *	138E							
" 1779	"	RF	"	30	3	20	150	125	100	30	50	10	2	10	-2					675 *	1.5	60 *	138E							
" 1780	"	"	Si. EP	25	3	15	150	125	100		50	10	2	10	-3					3000 *	1.5	20	276							